



**Ken Uchida**

**Ken Uchida** received B.S. degree in physics, M.S. and Ph.D. degrees in applied physics all from the University of Tokyo, Tokyo, Japan, in 1993, 1995, and 2002, respectively. In 1995, he joined the Research and Development Center, Toshiba Corporation, Kawasaki, Japan. He has studied carrier transport in nanoscale devices such as Single-Electron Devices, Schottky source/drain MOSFETs, Ultrathin-body SOI MOSFETs, Strained Silicon MOSFETs, Carbon Nanotube Transistors, and (110) Si MOSFETs. Since April 2008, he is an associate professor at Tokyo Institute of Technology, where he is researching on silicon-based nanoelectronics. Dr. Uchida is a member of the Japan Society of Applied Physics and IEEE Electron Devices Society. He won the 2003 IEEE EDS *Paul Rappaport Award*. He served as a subcommittee member as well as the subcommittee chair of IEEE International Electron Devices Meeting (IEDM). He was a program committee member of many international conferences.